Electronic Supplementary Information

Site controlled Red-Yellow-Green light emitting InGaN Quantum Disks on nano-tipped GaN rods

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The supplementary information contains 4 figures in support of the main text.

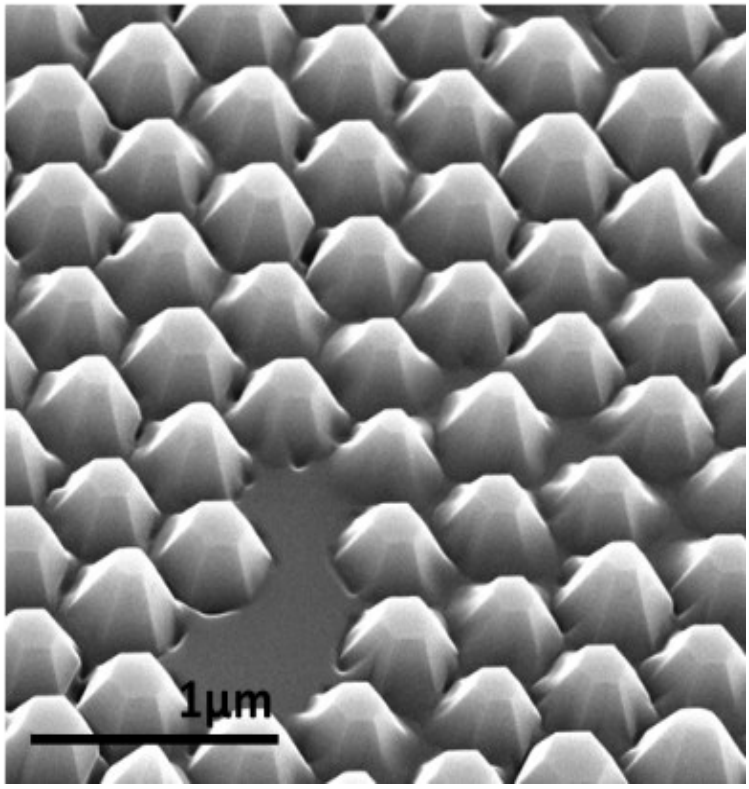

Figure S1. Top surface SEM of 300 nm GaN overgrowth on GaN etched nanorods with original etch depth of ~1 µm, showing the growth of GaN between adjacent nanorods causing coalesced regions.

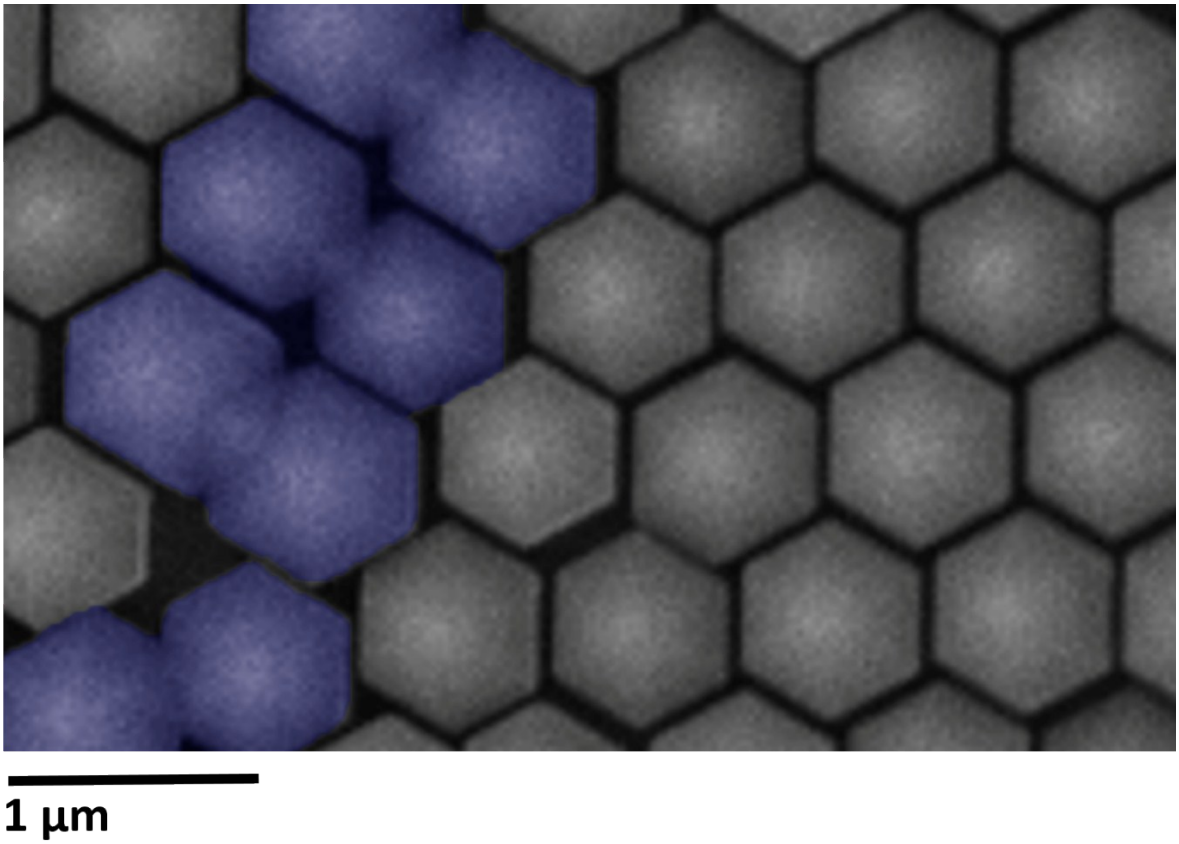

Figure S2. Top surface SEM of the GaN overgrown nanorods with the highlighted blue areas revealing the meeting point of "perfectly misaligned" adjacent GaN nanorods resulting in coalescing at the 11-20 facets.

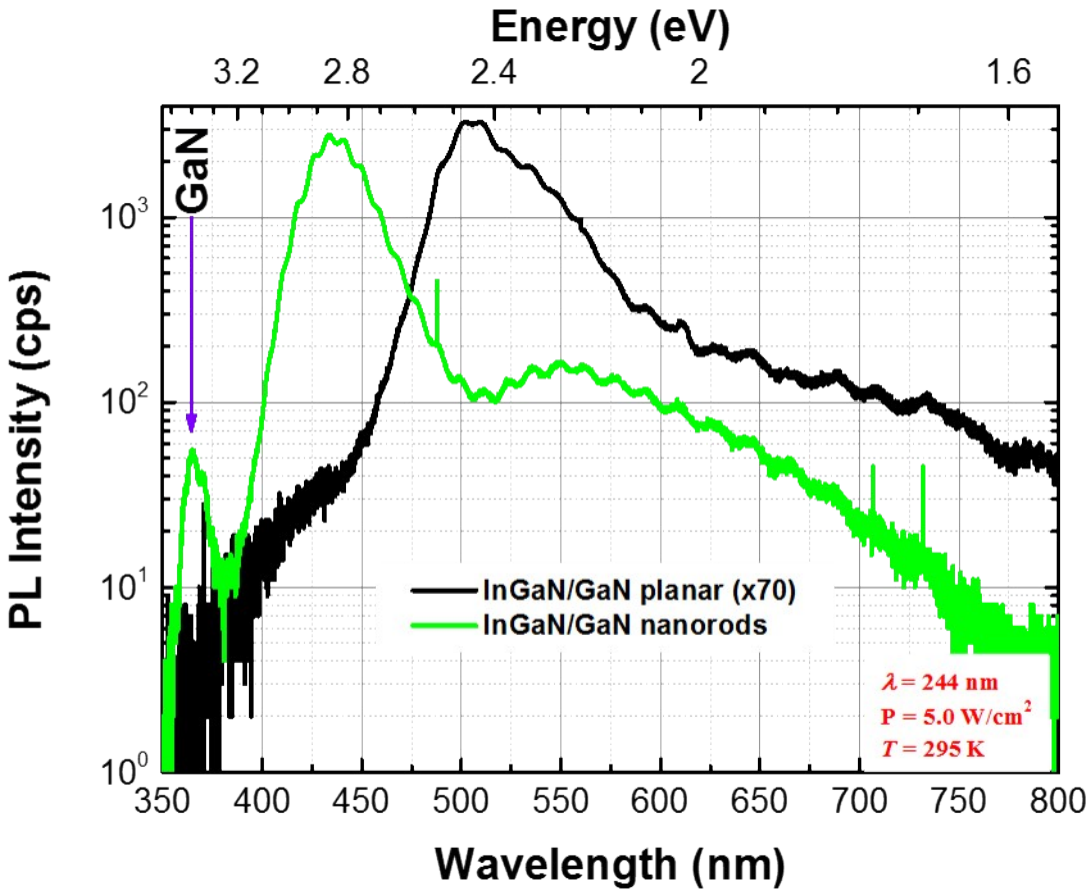

Figure S3. Room temperature PL of the InGaN/GaN MQWs grown on planar GaN (black line) and GaN nanorods (green line) with excitation at 244 nm. Measured intensity from the GaN planar sample was increased by a factor of 70.

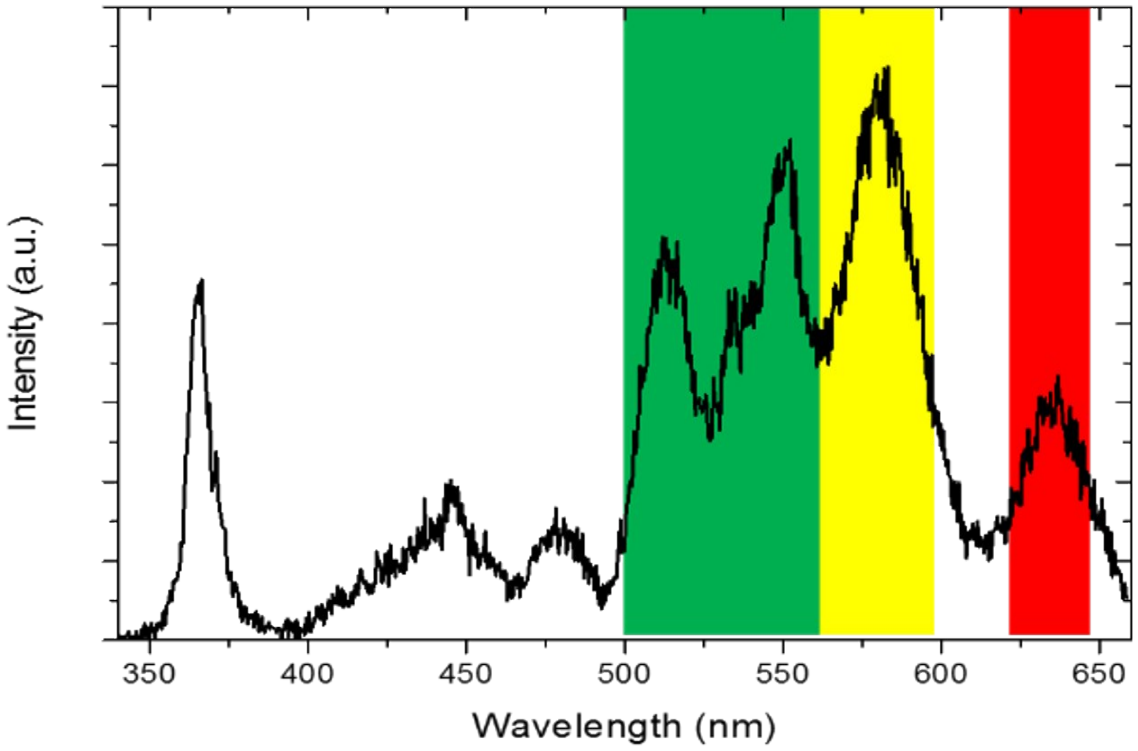

Figure S4. CL spectra of the 5 X InGaN MQWs grown on the GaN nanorods. The 5 peaks highlighted in green, yellow and red are the emission source from the c-plane MQWs.